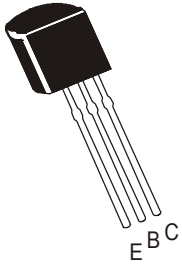


PNP SILICON PLANAR EPITAXIAL TRANSISTORS

**PN200
PN200A**

**TO-92
Plastic Package**



COMPLEMENTARY PN100, PN100A

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	V_{CEO}	35	V
Collector Base Voltage	V_{CBO}	60	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current Continuous	I_C	500	mA
Power Dissipation @ $T_a=25^\circ\text{C}$	P_D	625	mW
Operating And Storage Junction Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL RESISTANCE

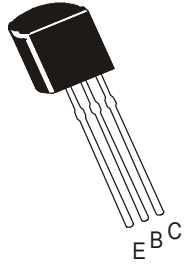
Junction to Ambient in free air	$R_{th(j-a)}$	200	$^\circ\text{C/W}$
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ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE		UNITS
			MIN	MAX	
Collector Emitter Breakdown Voltage	BV_{CEO}^*	$I_C=1\text{mA}, I_B=0$	35		V
Collector Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu\text{A}, I_E=0$	60		V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E=100\mu\text{A}, I_C=0$	5		V
Base Cut off Current	I_{CBO}	$V_{CB}=35\text{V}, I_E=0$		500	nA
Collector Emitter Saturation Voltage	$V_{CE(sat)}^*$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.4	V
	PN100, A	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
	PN200, A			2.0	V
Base Emitter Saturation Voltage	$V_{BE(sat)}^*$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.95	V
	PN100, A	$I_C=500\text{mA}, I_B=50\text{mA}$		1.2	V
	PN200, A			1.3	V

*Pulse Condition: = Width \leq 300ms, Duty Cycle \leq 2%.

PNP SILICON PLANAR EPITAXIAL TRANSISTORS



**PN200
PN200A**

**TO-92
Plastic Package**

COMPLEMENTARY PN100, PN100A

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

DESCRIPTION	SYMBOL	TEST CONDITION	PN100	PN100A	PN200	PN200A
DC Current Gain	h_{FE}^*	$I_C=1\text{mA}, V_{CE}=1\text{V}$	>40	>40	>40	>40
		$I_C=10\text{mA}, V_{CE}=1\text{V}$	100-450	300-600	100-450	300-600
		$I_C=150\text{mA}, V_{CE}=1\text{V}^*$	>100	>100		
		$I_C=150\text{mA}, V_{CE}=2\text{V}^*$			>100	>100

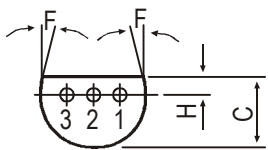
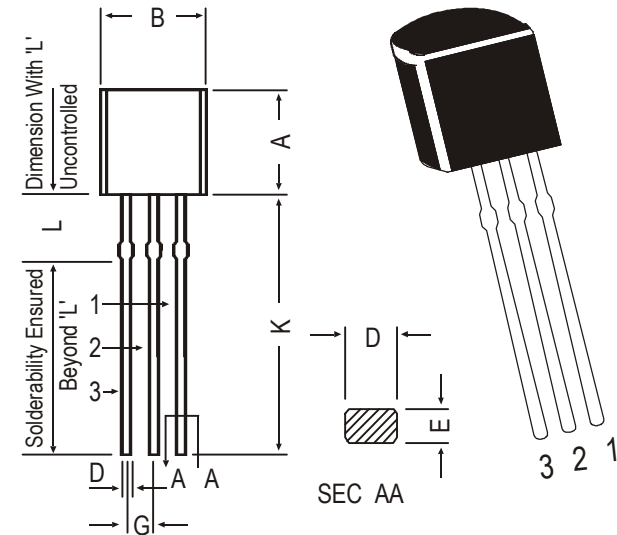
DYNAMIC CHARACTERISTICS

Transition Frequency	f_T	$I_C=20\text{mA}, V_{CE}=10\text{V}$				
		$f=100\text{MHz}$				
	PN100, A		>200			MHz
	PN200, A		>150			MHz

*Pulse Condition: = Width \leq 300ms, Duty Cycle \leq 2%.

TO-92 Plastic Package

TO-92 Transistors in Tape and Ammo Pack

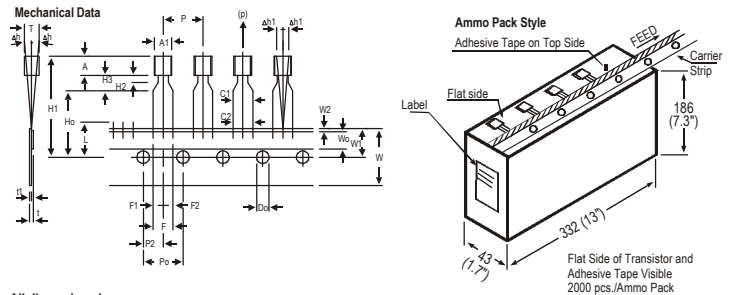


PIN CONFIGURATION

1. COLLECTOR
2. BASE
3. EMITTER

DIM	MIN.	MAX.
A	4.32	5.33
B	4.45	5.20
C	3.18	4.19
D	0.41	0.55
E	0.35	0.50
F	5 DEG	
G	1.14	1.40
H	1.14	1.53
K	12.70	—
L	1.982	2.082

All diminsions in mm.



All dimensions in mm

ITEM	SYMBOL	SPECIFICATION				REMARKS
		MIN.	NOM.	MAX.	TOL.	
BODY WIDTH	A1	4.0	4.8			
BODY HEIGHT	A	4.8	5.2			
BODY THICKNESS	T	3.9	4.2			
PITCH OF COMPONENT	P	12.7			± 1.0	
FEED HOLE PITCH	Po	12.7			± 0.3	CUMULATIVE PITCH ERROR 1.0 mm/20 PITCH
FEED HOLE CENTRE TO COMPONENT CENTRE	P2	6.35			± 0.4	TO BE MEASURED AT BOTTOM OF CLINCH
DISTANCE BETWEEN OUTER LEADS	F	5.08			+ 0.6 - 0.2	
COMPONENT ALIGNMENT SIDE VIEW	Δh	0	1.0			AT TOP OF BODY
COMPONENT ALIGNMENT FRONT VIEW	Δh1	0	1.3			AT TOP OF BODY
TAPE WIDTH	W	18			± 0.5	
HOLD-DOWN TAPE WIDTH	Wo	6			± 0.2	
HOLE POSITION	W1	9			+ 0.7 - 0.5	
HOLD-DOWN TAPE POSITION	W2	0.5			± 0.2	
LEAD WIRE CLINCH HEIGHT	Ho	16			± 0.5	
COMPONENT HEIGHT	H1		23.25			
LENGTH OF SNIPPED LEADS	L		11.0			
FEED HOLE DIAMETER	Do	4			± 0.2	
TOTAL TAPE THICKNESS	t		1.2			t1 0.3-0.6
LEAD - TO - LEAD DISTANCE	F1, F2	2.54			+ 0.4 - 0.1	
STAND OFF	H2	0.45	1.45			
CLINCH HEIGHT	H3		3.0			
LEAD PARALLELISM	C1 - C2		0.22			
PULL - OUT FORCE	(P)	6N				

NOTES

1. Maximum alignment deviation between leads will not be greater than 0.2mm.
2. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
3. Holddown tape will not exceed beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
4. There will be no more than three (3) consecutive missing components in a tape.
5. A tape trailer, having at least three feed holes are provided after the last component in a tape.
6. Splices should not interfere with the sprocket feed holes.

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-92 Bulk	1K/polybag	200 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	23 kgs
TO-92 T&A	2K/ammo box	645 gm/2K pcs	12.5" x 8" x 1.8"	2K	17" x 15" x 13.5"	32K	12.5 kgs

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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